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(54) Title: METHODS FOR CONDITIONING POLISHING PADS

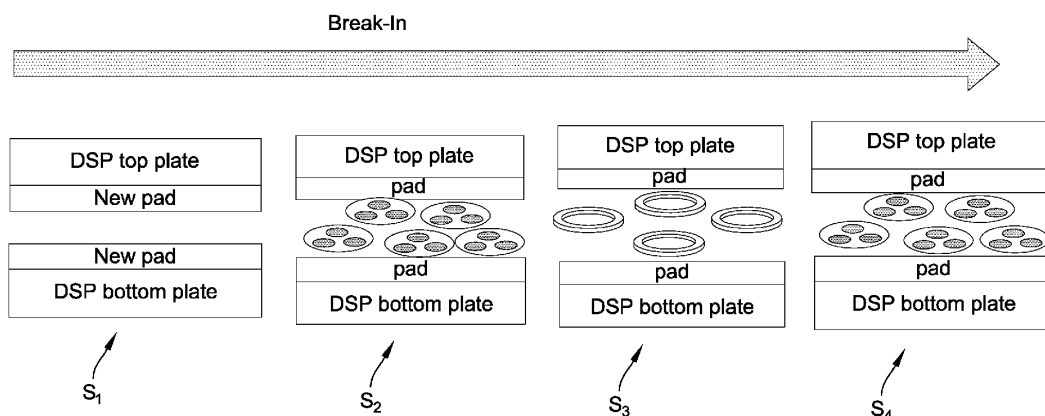


FIG. 3

(57) Abstract: Methods for breaking-in new polishing pads of a double-side polishing apparatus for polishing substrates such as single crystal silicon wafers are disclosed. The methods may involve contacting the new polishing pads with a conditioning substrate such as a substrate that includes diamonds at the surface of the substrate. Conditioning methods may also involve contacting the new polishing pad with sacrificial substrates.

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